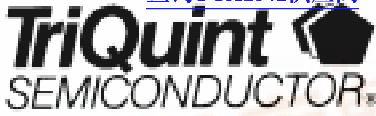
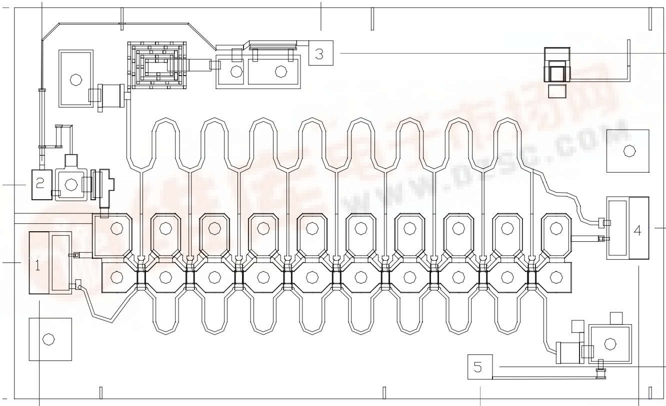
查询TGA1342供应商

捷多邦，专业PCB打样工厂，24小时加急出货



Advance Product Information

2 -20 GHz Wideband AGC Amplifier TGA1342-EPU



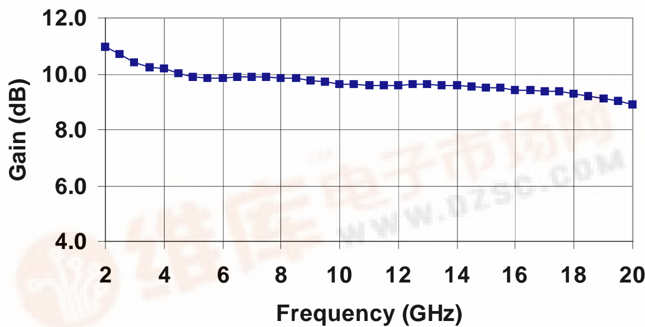
Key Features and Performance

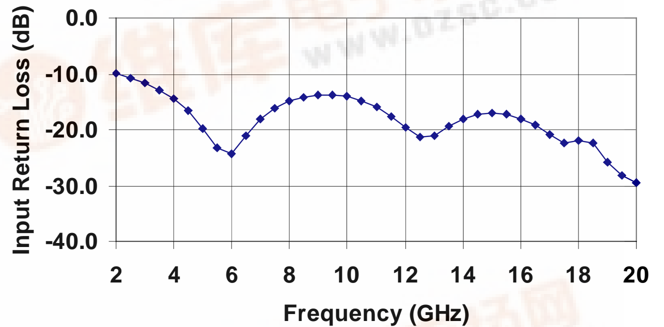
- 0.5 um MESFET Technology
- 9 dB Nominal Gain
- 3.5 dB NF Typical Midband
- 17.5 dBm Nominal Pout @ P1dB
- Bias 5-8V @ 60 mA
- Dimensions 3.378mm x 2.032mm

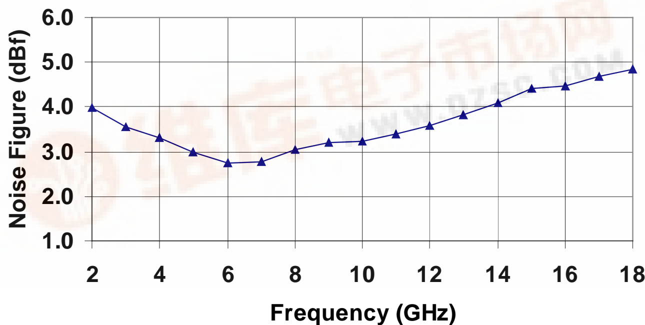
Primary Applications

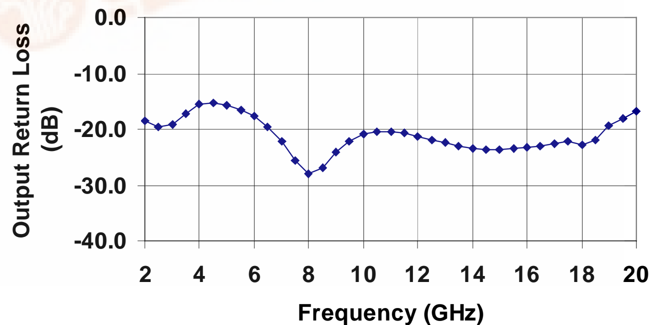
- Wideband Gain Block Amplifier
- Wideband Low Noise Amplifier

Typical Electrical Characteristics





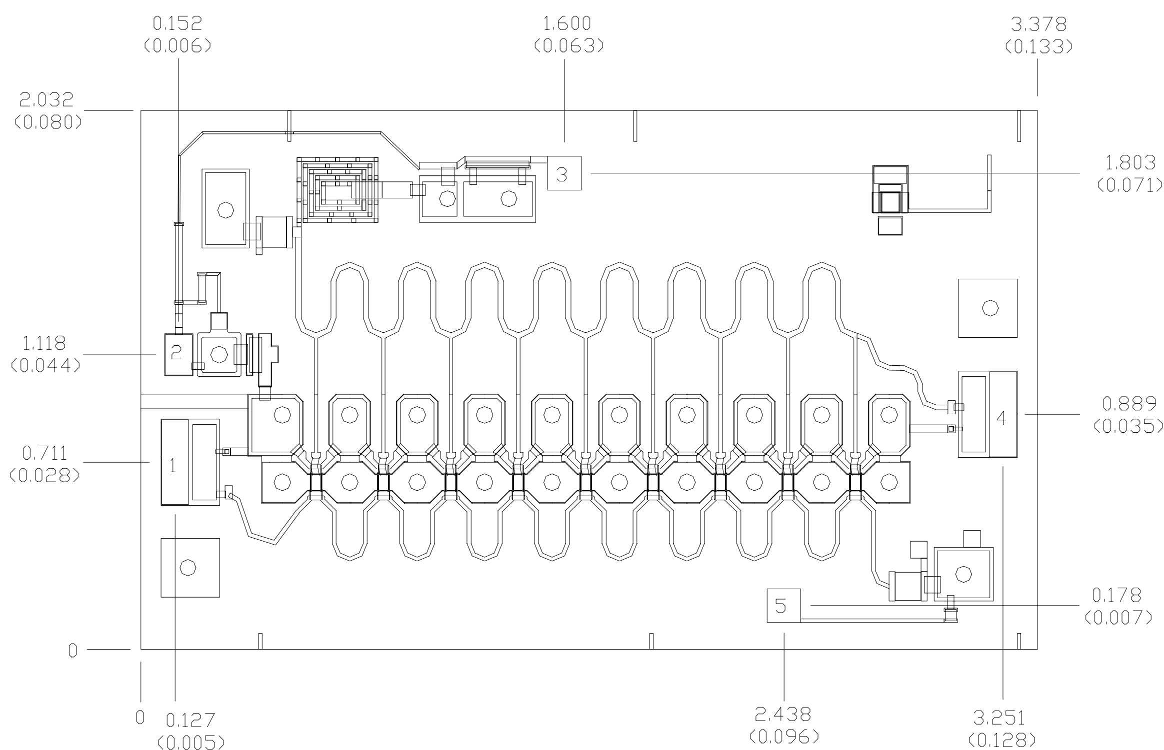




Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice

Advance Product Information

Mechanical Characteristics



Units: millimeters (inches)
Thickness: 0.1016 (0.004) (reference only)
Chip edge to bond pad dimensions are shown to center of bond pads.
Chip size tolerance: ± 0.0508 (0.002)

Bond Pad #1 (RF Input)	0.102 x 0.330 (0.004 x 0.013)
Bond Pad #2 (Vg2)(Vcontrol)	0.102 x 0.152 (0.004 x 0.006)
Bond Pad #3 (Vd)	0.127 x 0.127 (0.005 x 0.005)
Bond Pad #4 (RF Output)	0.102 x 0.330 (0.004 x 0.013)
Bond Pad #5 (Vg1)	0.127 x 0.127 (0.005 x 0.005)

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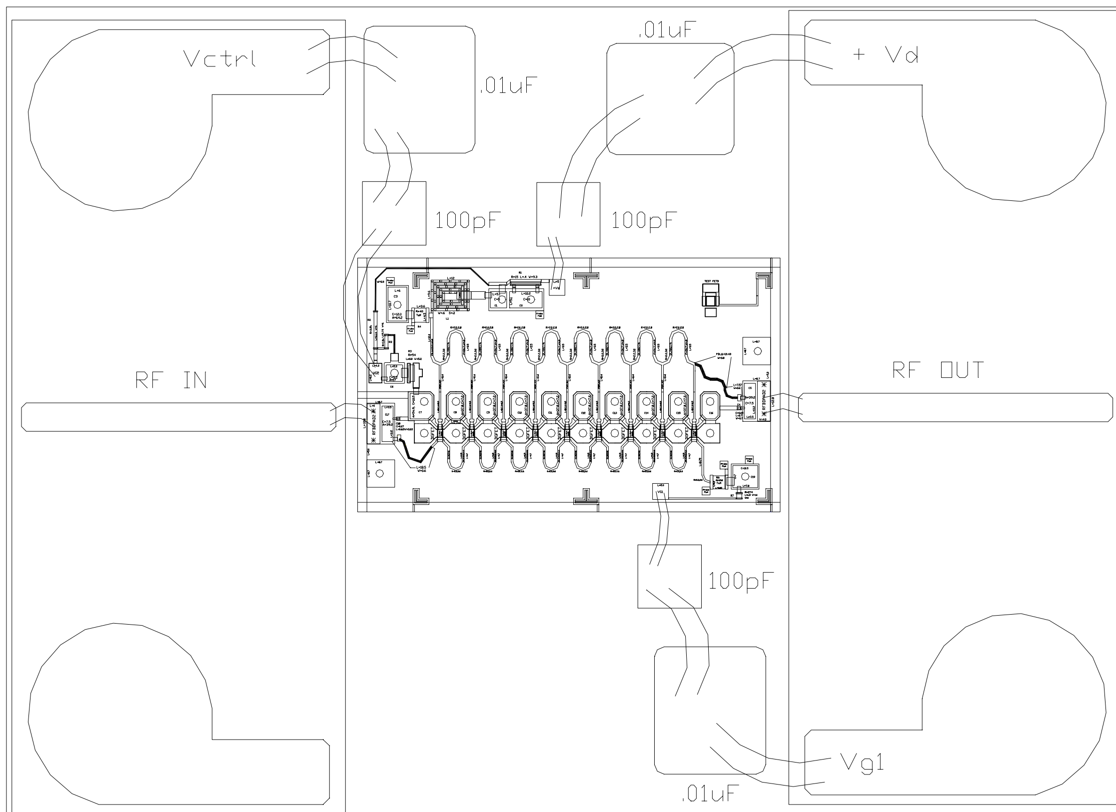
TriQuint SEMICONDUCTOR

Chip Assembly and Bonding Diagram



Reflow process assembly notes:

- AuSn (80/20) solder with limited exposure to temperatures at or above 300°C
- alloy station or conveyor furnace with reducing atmosphere
- no fluxes should be utilized
- coefficient of thermal expansion matching is critical for long-term reliability
- storage in dry nitrogen atmosphere

Component placement and adhesive attachment assembly notes:

- vacuum pencils and/or vacuum collets preferred method of pick up
- avoidance of air bridges during placement
- force impact critical during auto placement
- organic attachment can be used in low-power applications
- curing should be done in a convection oven; proper exhaust is a safety concern
- microwave or radiant curing should not be used because of differential heating
- coefficient of thermal expansion matching is critical

Interconnect process assembly notes:

- thermosonic ball bonding is the preferred interconnect technique
- force, time, and ultrasonics are critical parameters
- aluminum wire should not be used
- discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire
- maximum stage temperature: 200°C